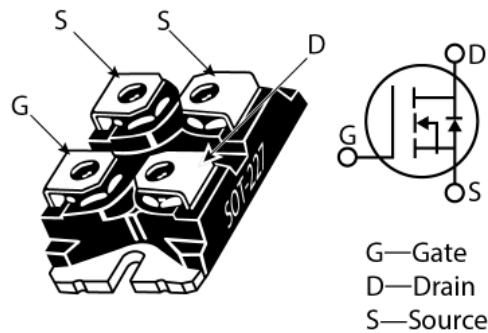


MSC017SMA120J Silicon Carbide N-Channel Power MOSFET

Product Overview

The silicon carbide (SiC) power MOSFET product line from Microsemi increases the performance over silicon MOSFET and silicon IGBT solutions while lowering the total cost of ownership for high-voltage applications. The MSC017SMA120J device is a 1200 V, 17 mΩ SiC MOSFET in a SOT-227 package.



Features

The following are key features of the MSC017SMA120J device:

- Low capacitances and low gate charge
- Fast switching speed due to low internal gate resistance (ESR)
- Stable operation at high junction temperature, $T_{J(max)} = 175\text{ °C}$
- Fast and reliable body diode
- Superior avalanche ruggedness
- RoHS compliant
- Isolated voltage to 2500 V

Benefits

The following are benefits of the MSC017SMA120J device:

- High efficiency to enable lighter, more compact system
- Simple to drive and easy to parallel
- Improved thermal capabilities and lower switching losses
- Eliminates the need for external freewheeling diode
- Lower system cost of ownership

Applications

The MSC017SMA120J device is designed for the following applications:

- PV inverter, converter, and industrial motor drives
- Smart grid transmission and distribution
- Induction heating and welding
- H/EV powertrain and EV charger
- Power supply and distribution

Device Specifications

This section shows the specifications of the MSC017SMA120J device.

Absolute Maximum Ratings

The following table shows the absolute maximum ratings of the MSC017SMA120J device.

Table 1 • Absolute Maximum Ratings

| Symbol | Parameter | Ratings | Unit |
|------------------|---|-----------|------|
| V _{DSS} | Drain source voltage | 1200 | V |
| I _D | Continuous drain current at T _C = 25 °C | 88 | A |
| | Continuous drain current at T _C = 100 °C | 62 | |
| | Pulsed drain current ¹ | 280 | |
| V _{GS} | Gate-source voltage | 23 to -10 | V |
| P _D | Total power dissipation at T _C = 25 °C | 278 | W |
| | Linear derating factor | 3.33 | W/°C |

Note:

1. Repetitive rating: pulse width and case temperature limited by maximum junction temperature.

The following table shows the thermal and mechanical characteristics of the MSC017SMA120J device.

Table 2 • Thermal and Mechanical Characteristics

| Symbol | Characteristic | Min | Typ | Max | Unit |
|-----------------|--|------|------|------|-----------------------------|
| $R_{\theta JC}$ | Junction-to-case thermal resistance | | 0.36 | 0.54 | $^{\circ}\text{C}/\text{W}$ |
| T_J | Operating junction temperature | -55 | | 175 | $^{\circ}\text{C}$ |
| T_{STG} | Storage temperature | -55 | | 150 | |
| T_L | Soldering temperature for 10 seconds (1.6 mm from case) | | | 300 | $^{\circ}\text{C}$ |
| $V_{ISOLATION}$ | RMS voltage (50 Hz–60 Hz sinusoidal waveform from terminals to mounting base for 1 minute) | 2500 | | | V |
| | Mounting torque, M4 screw | | | 10 | lbf-in |
| | | | | 1.1 | N-m |
| Wt | Package weight | | 1.03 | | oz |
| | | | 29.2 | | g |

Electrical Performance

The following table shows the static characteristics of the MSC017SMA120J device. $T_J = 25^{\circ}\text{C}$ unless otherwise specified.

Table 3 • Static Characteristics

| Symbol | Characteristic | Test Conditions | Min | Typ | Max | Unit |
|--------------------------------|---|--|------|------|-----------|------------------------|
| $V_{(BR)DSS}$ | Drain-source breakdown voltage | $V_{GS} = 0\text{ V}, I_D = 100\ \mu\text{A}$ | 1200 | | | V |
| $R_{DS(on)}$ | Drain-source on resistance ¹ | $V_{GS} = 20\text{ V}, I_D = 40\text{ A}$ | | 17.6 | 22 | m Ω |
| $V_{GS(th)}$ | Gate-source threshold voltage | $V_{GS} = V_{DS}, I_D = 4.5\text{ mA}$ | 1.9 | 2.7 | | V |
| $\Delta V_{GS(th)}/\Delta T_J$ | Threshold voltage coefficient | $V_{GS} = V_{DS}, I_D = 4.5\text{ mA}$ | | -4.6 | | mV/ $^{\circ}\text{C}$ |
| I_{DSS} | Zero gate voltage drain current | $V_{DS} = 1200\text{ V}, V_{GS} = 0\text{ V}$ | | | 100 | μA |
| | | $V_{DS} = 1200\text{ V}, V_{GS} = 0\text{ V}$ $T_J = 125^{\circ}\text{C}$ | | | 500 | |
| I_{GSS} | Gate-source leakage current | $V_{GS} = 20\text{ V}/-10\text{ V}$ | | | ± 100 | nA |

Note:

1. Pulse test: pulse width < 380 μs , duty cycle < 2%.

The following table shows the dynamic characteristics of the MSC017SMA120J device. $T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified.

Table 4 • Dynamic Characteristics

| Symbol | Characteristic | Test Conditions | Min | Typ | Max | Unit |
|--------------|--------------------------------|--|-----|------|-----|---------------|
| C_{iss} | Input capacitance | $V_{GS} = 0\text{ V}, V_{DD} = 1000\text{ V}$ $V_{AC} = 25\text{ mV}, f = 1\text{ MHz}$ | | 5280 | | pF |
| C_{rss} | Reverse transfer capacitance | | | 12 | | |
| C_{oss} | Output capacitance | | | 265 | | |
| Q_g | Total gate charge | $V_{GS} = -5\text{ V}/20\text{ V}, V_{DD} = 800\text{ V}$ $I_D = 40\text{ A}$ | | 249 | | nC |
| Q_{gs} | Gate-source charge | | | 63 | | |
| Q_{gd} | Gate-drain charge | | | 32 | | |
| $t_{d(on)}$ | Turn-on delay time | $V_{DD} = 800\text{ V}, V_{GS} = -5\text{ V}/20\text{ V},$ $I_D = 50\text{ A}, R_{g(ext)} = 4.0\text{ }\Omega,$ Freewheeling diode = MSC017SMA120J ($V_{GS} = -5\text{ V}$) | | TBD | | ns |
| t_f | Voltage fall time | | | TBD | | |
| $t_{d(off)}$ | Turn-off delay time | | | TBD | | |
| t_r | Voltage rise time | | | TBD | | |
| E_{on} | Turn-on switching energy | | | TBD | | |
| E_{off} | Turn-off switching energy | | TBD | | | |
| $t_{d(on)}$ | Turn-on delay time | $V_{DD} = 800\text{ V}, V_{GS} = -5\text{ V}/20\text{ V},$ $I_D = 50\text{ A}, R_{g(ext)} = 4.0\text{ }\Omega$ Freewheeling diode = MSC050SDA120B | | TBD | | ns |
| t_f | Voltage fall time | | | TBD | | |
| $t_{d(off)}$ | Turn-off delay time | | | TBD | | |
| t_r | Voltage rise time | | | TBD | | |
| E_{on} | Turn-on switching energy | | | TBD | | |
| E_{off} | Turn-off switching energy | | TBD | | | |
| ESR | Equivalent series resistance | $f = 1\text{ MHz}, 25\text{ mV}, \text{ drain short}$ | | 0.71 | | Ω |
| SCWT | Short circuit withstand time | $V_{DS} = 960\text{ V}, V_{GS} = 20\text{ V}$ | | 3 | | μs |
| E_{AS} | Avalanche energy, single pulse | $V_{DS} = 150\text{ V}, I_D = 30\text{ A}$ | | 3500 | | mJ |

The following table shows the body diode characteristics of the MSC017SMA120J device. $T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified.

Table 5 • Body Diode Characteristics

| Symbol | Characteristic | Test Conditions | Min | Typ | Max | Unit |
|-----------|--------------------------|---|-----|-----|-----|------|
| V_{SD} | Diode forward voltage | $I_{SD} = 40\text{ A}, V_{GS} = 0\text{ V}$ | | 3.5 | | V |
| | | $I_{SD} = 40\text{ A}, V_{GS} = -5\text{ V}$ | | 3.9 | | V |
| t_{rr} | Reverse recovery time | $I_{SD} = 50\text{ A}, V_{GS} = -5\text{ V},$ Drive $R_g = 4\ \Omega$ $V_{DD} = 800\text{ V}, dI/dt = -2500\text{ A}/\mu\text{s}$ | | 40 | | ns |
| Q_{rr} | Reverse recovery charge | | | 490 | | nC |
| I_{RRM} | Reverse recovery current | | | 22 | | A |

Typical Performance Curves

This section shows the typical performance curves of the MSC017SMA120J device.

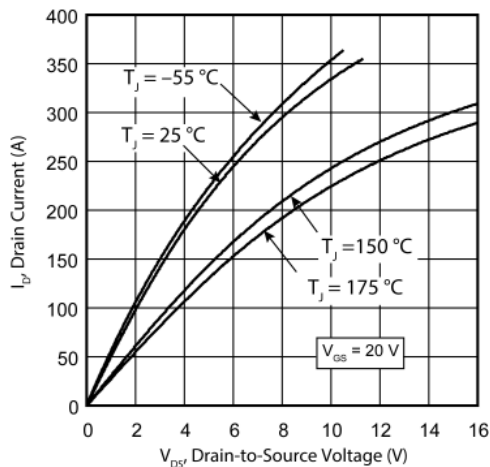


Figure 1 • Drain Current vs. V_{DS}

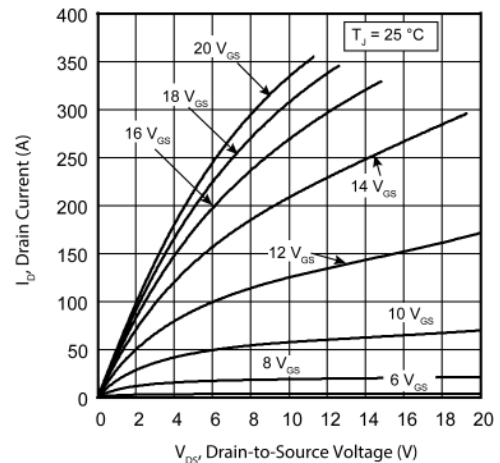


Figure 2 • Drain Current vs. V_{DS}

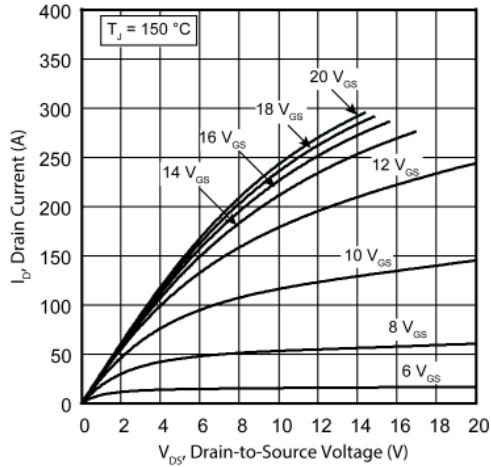


Figure 3 • Drain Current vs. V_{DS}

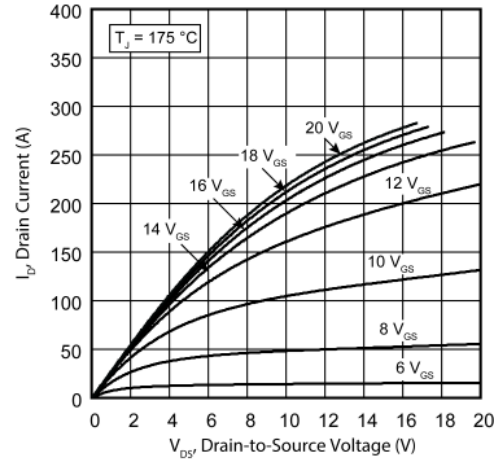


Figure 4 • Drain Current vs. V_{DS}

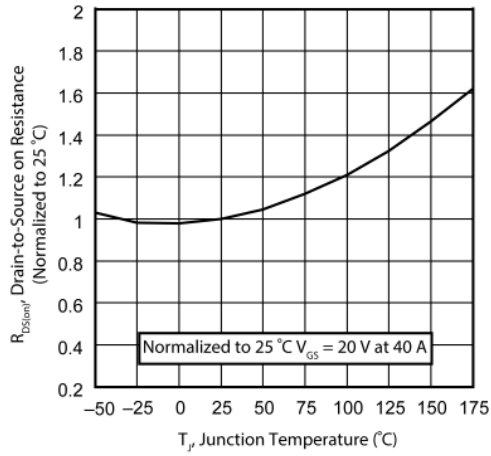


Figure 5 • $R_{DS(on)}$ vs. Junction Temperature

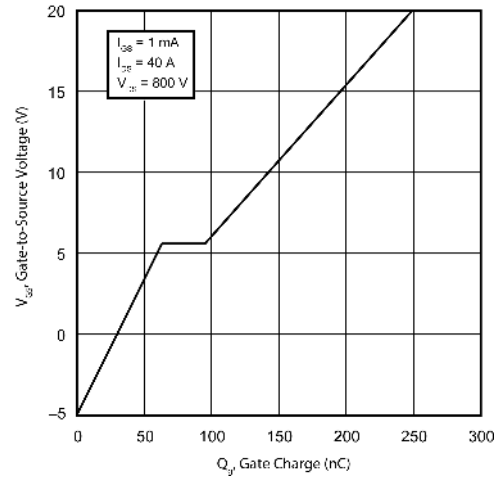


Figure 6 • Gate Charge Characteristics

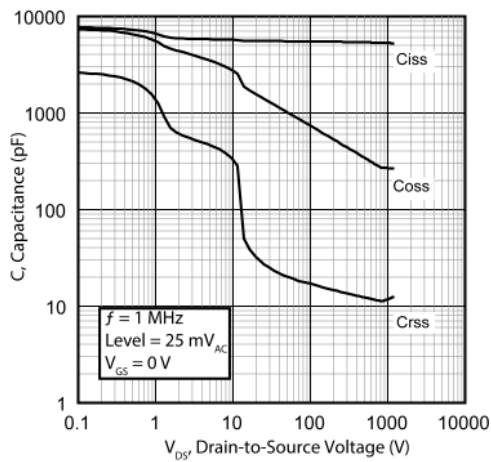


Figure 7 • Capacitance vs. Drain-to-Source Voltage

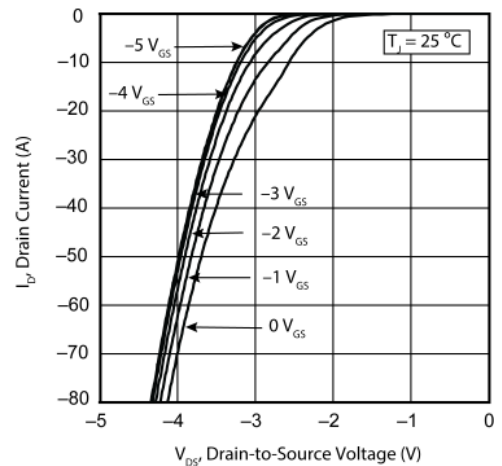


Figure 8 • I_D vs. V_{DS} 3rd Quadrant Conduction

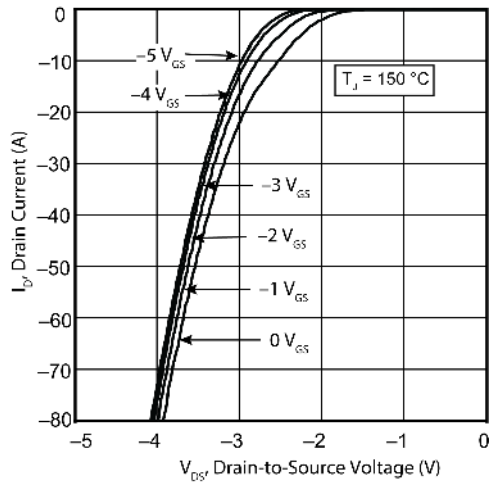


Figure 9 • I_D vs. V_{DS} 3rd Quadrant Conduction

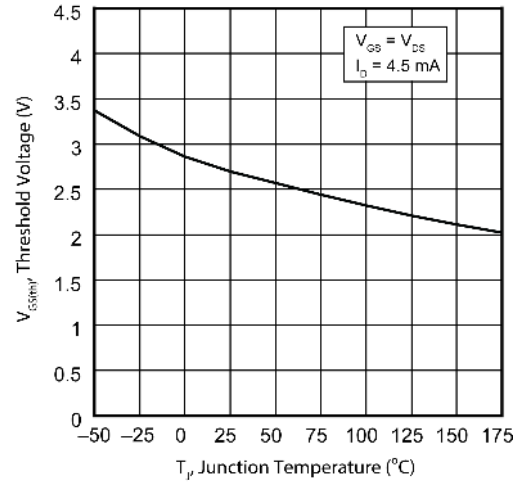


Figure 10 • Threshold Voltage vs. Junction Temp.

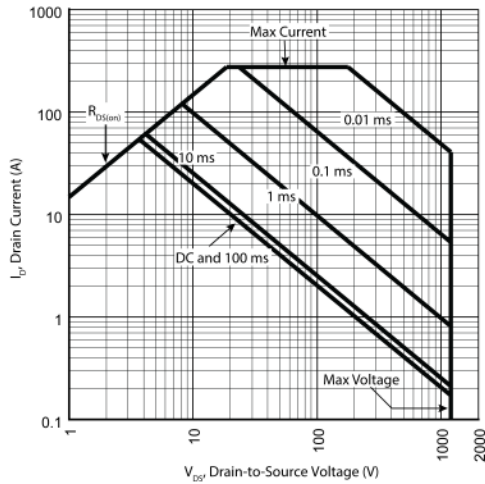


Figure 11 • Forward Safe Operating Area

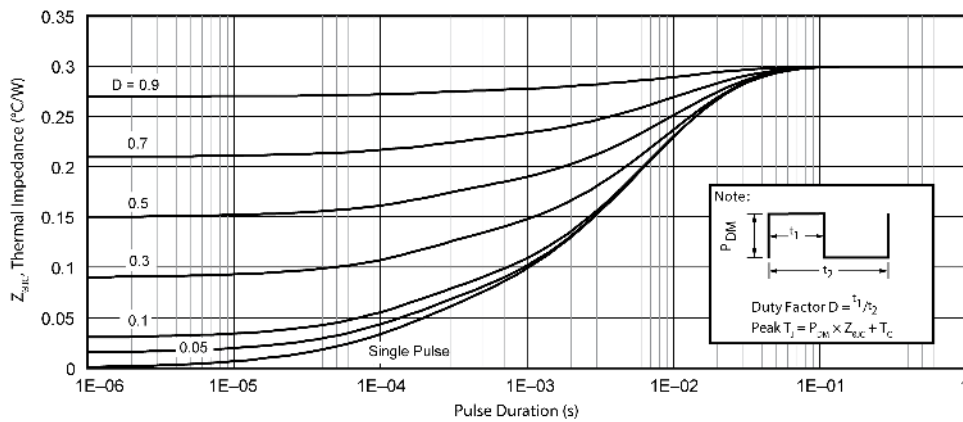


Figure 12 • Maximum Transient Thermal Impedance

Package Specification

This section shows the package specification of the MSC017SMA120J device.

Package Outline Drawing

The following figure illustrates the SOT-227 package outline of the MSC017SMA120J device. The dimensions in the figure below are in millimeters and (inches).

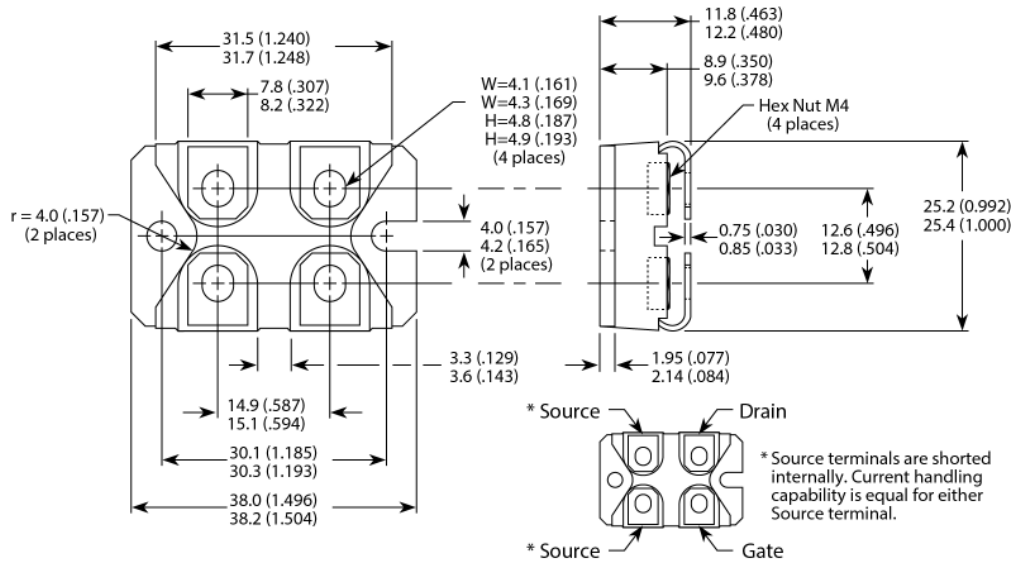


Figure 13 • Package Outline Drawing

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